

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

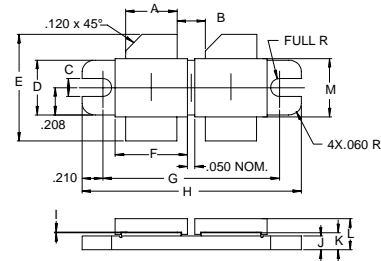
The **ASI TVU150A** is Designed for Television Band IV & V Applications up to 860 MHz.

FEATURES:

- Common Emitter
- $P_G = 6.5$ dB at 150 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	3.0 V
P_{DISS}	310 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.55 °C/W

PACKAGE STYLE .450 BAL FLG(B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L	.250 / 6.35	
M	.445 / 11.30	.457 / 11.61

ORDER CODE: ASI10653
CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	60			V
BV_{CEO}	$I_C = 100$ mA	30			V
BV_{EBO}	$I_E = 10$ mA	3.0			V
I_{CES}	$V_{CE} = 28$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 3.0$ A	15		70	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			100	pF
P_G	$V_{CE} = 28$ V $I_C = 2 \times 500$ mA $f = 860$ MHz $P_{OUT} = 150$ W	6.5			dB